Power MOSFET 100V, 3.0mΩ, 180A, N-Channel



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RDS(on) Max

3.0mΩ@ 15V

3.5mΩ@ 10V

VDSS

100V

Features

- Ultra Low On-Resistance
- Low Gate Charge
- High Speed Switching
- 100% Avalanche Test
- Pb-Free and RoHS compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C (Note 1)

U				
Parameter	Symbol	Value	Unit	
Drain to Source Voltage	VDSS	100	V	
Gate to Source Voltage	VGSS	±20	V	
Drain Current (DC)	ID	180	А	
Drain Current (DC) Limited by Package	IDL	100	А	
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I _{DP}	600	A	
Power Dissipation	Do	2.1	10/	
Tc=25°C	PD	200	W	
Junction Temperature	Tj	175	°C	
Storage Temperature	Tstg	-55 to +175	°C	
Source Current (Body Diode)	IS	100	А	
Avalanche Energy (Single Pulse) (Note 2)	EAS	451	mJ	
Lead Temperature for Soldering Purposes, 3mm from Case for 10 Seconds	TL	260	°C	

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

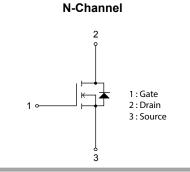
2 : V_{DD}=48V, L=100µH, I_{AV}=70A (Fig.1)

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Case Steady State	$R_{\theta JC}$	0.75	°C/W
Junction to Ambient (Note 3)	$R_{\theta JA}$	71.4	

Note 3 : Insertion mounted

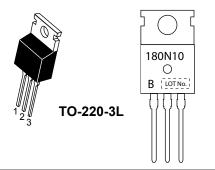
Electrical Connection



Marking

ID Max

180A



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Electrical Characteristics at $Ta = 25^{\circ}C$ (Note 4)

Description	Symphol	Conditions	Value			
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =10mA, V _{GS} =0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			10	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±20V, V _{DS} =0V			±200	nA
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	2		4	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =50A		150		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =50A, V _{GS} =15V		2.5	3.0	mΩ
	R _{DS} (on)2	I _D =50A, V _{GS} =10V		2.7	3.5	mΩ
Input Capacitance	Ciss			6,950		pF
Output Capacitance	Coss	V _{DS} =50V, f=1MHz		3,000		pF
Reverse Transfer Capacitance	Crss			15		pF
Turn-ON Delay Time	t _d (on)			95		ns
Rise Time	tr	1		320		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		185		ns
Fall Time	tf			130		ns
Total Gate Charge	Qg			95		nC
Gate to Source Charge	Qgs	V _{DS} =48V, V _{GS} =10V, I _D =100A		31		nC
Gate to Drain "Miller" Charge	Qgd	1		26		nC
Forward Diode Voltage	V _{SD}	I _S =100A, V _{GS} =0V		0.9	1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		150		ns
Reverse Recovery Charge	Q _{rr}	- I _S =100A, V _{GS} =0V, V _{DD} =50V, di/dt=100A/μs		580		nC

Note 4 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig.1 Unclamped Inductive Switching Test Circuit

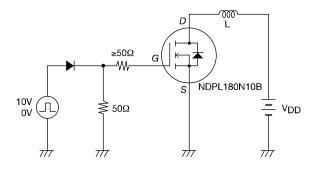


Fig.2 Switching Time Test Circuit

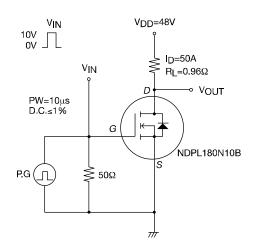
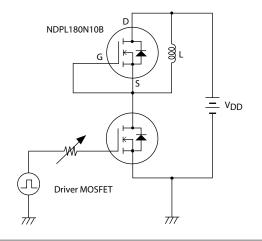


Fig.3 Reverse Recovery Time Test Circuit



6

150

1.2

80

100

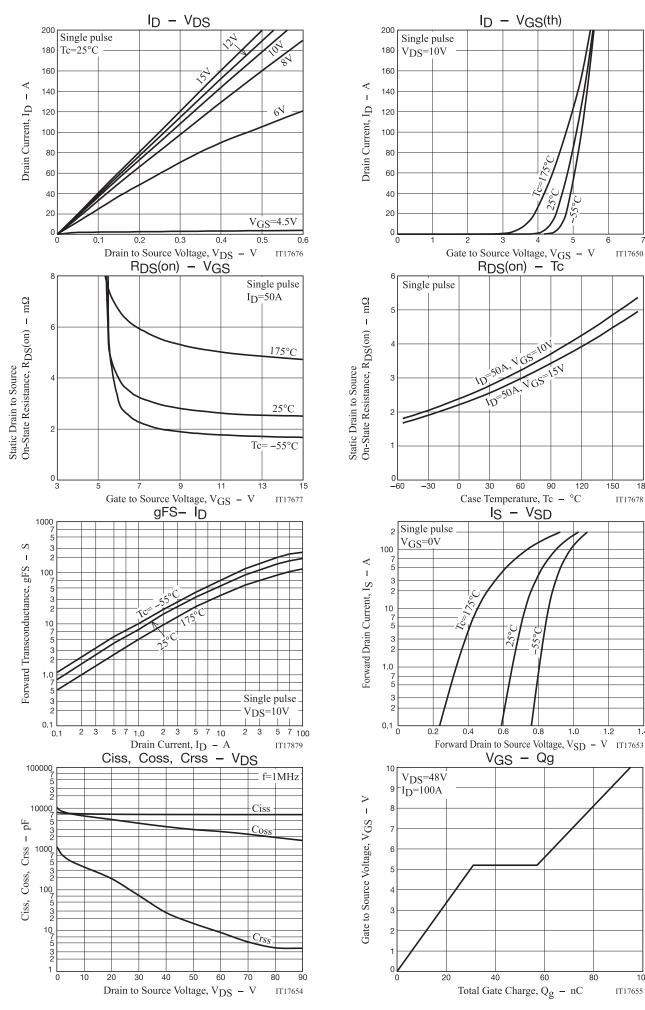
IT17655

1.4

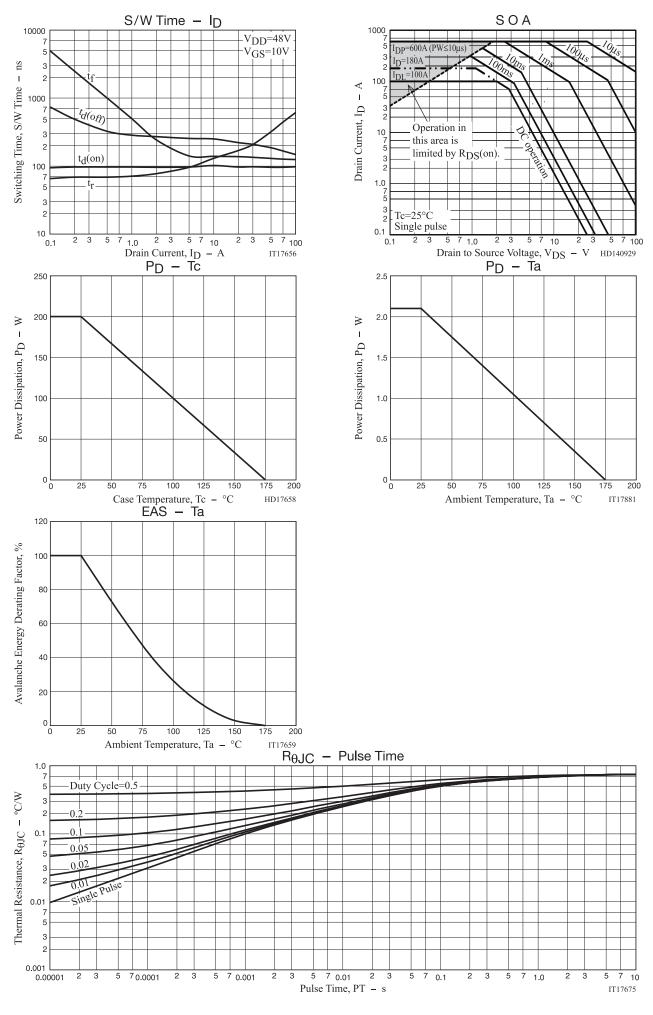
IT17678

180

IT17650



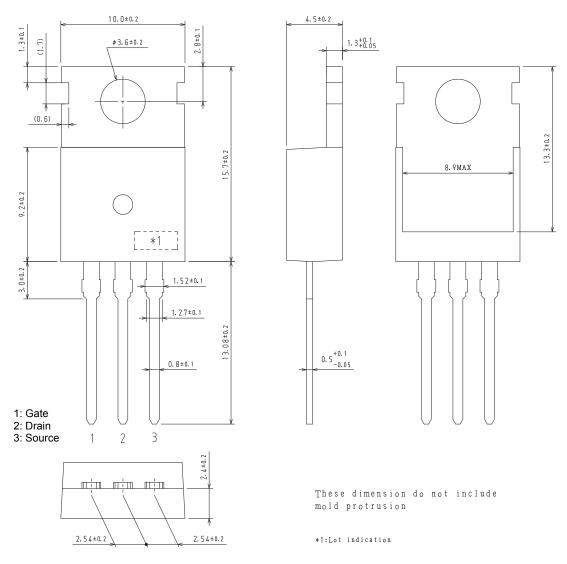
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Package Dimensions

unit : mm

TO-220, 3-Lead / TO-220-3L CASE 221AU ISSUE O



ORDERING INFORMATION

Device	Package	Shipping	Note	
NDPL180N10BG	TO-220, 3-Lead TO-220-3L	50 pcs. / Tube	Pb-Free	

Note on usage : Since the NDPL180N10B is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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